

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a substrate and a MISFET including source-drain regions formed in the substrate and a gate electrode formed on the substrate with a gate insulating film interposed therebetween. 5 The gate electrode is formed of a metal oxynitride film containing a metal-oxygen-nitrogen bond chain. Alternatively, the gate insulating film is formed of a nitrided metal silicate film containing at least one 10 of a metal-oxygen-nitrogen bond chain and a silicon-oxygen-nitrogen bond chain.